- Can use RF and radiant heating to reduce temp diff.
- Also can use wafer pockets on susceptor.

- Stacking faults
  - Result from microscopic steps on substrate.
    - Impurities ($SiO_2$, $N_2O$, Cu ...)

- Reducing defects
  - Use denuded zone and $O_2$ gettering prior to deposition.
  - Can deposit $SiGe$ alloy and then deposit $Si$ EPI layer. The misfit dislocations resulting act as getter sites for metallic contaminants.

- Pattern shift, distortion, washout.
  - The image of a surface step over a B.L. can change.